

What is claimed is:

1. A method of manufacturing a semiconductor device, comprising:

5 a step of forming an oxidation proof layer including an aperture on a silicon substrate;

a step of forming a field oxide for a device isolation thermally oxidizing silicon at the aperture;

10 a step of depositing a protective layer thicker than a thickness of said oxidation proof layer on said oxidation proof layer and on said field oxide, said protective layer being composed of such a selective removable material as to establish a condition under which said oxidation proof layer is selectively removed;

15 a step of making said protective layer residual on only the surface of said field oxide by removing a part of said protective layer deposited in said depositing step till the surface of the said oxidation proof layer is exposed; and

20 a step of removing said oxidation proof layer.

2. A method of manufacturing a semiconductor device according to claim 1, wherein said protective layer is composed of polysilicon.

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